

## OPERATIONAL AMPLIFIER

The TAA241 is a silicon monolithic integrated d. c. amplifier in a TO-99 metal envelope for applications in the temperature range from 0 to 70 °C.

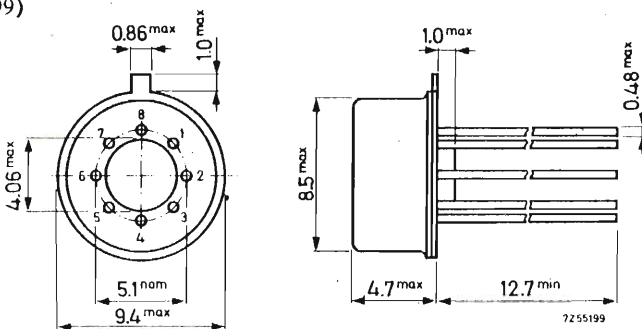
### QUICK REFERENCE DATA

Positive supply voltage	$V_P$	12 V
Negative supply voltage	$-V_N$	6 V
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Characteristics at $T_{amb} = 25\text{ }^\circ\text{C}$		
Voltage gain	$G_V$	typ. 3400
Common mode rejection ratio	CMRR	typ. 92 dB
Input offset voltage drift	$\frac{\Delta V_{i0}}{\Delta T}$	typ. 5 $\mu\text{V}/^\circ\text{C}$
Differential input resistance	$R_i$	typ. 32 k $\Omega$
Output resistance	$R_o$	typ. 200 $\Omega$
Power dissipation	$P_{tot}$	typ. 90 mW

### PACKAGE OUTLINE

Dimensions in mm

XA8 (TO-99)



**RATINGS** Limiting values in accordance with the Absolute Maximum System (IEC134)

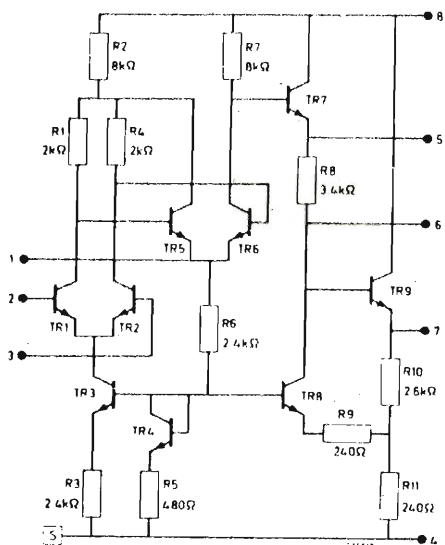
Voltages

Total supply voltage	$V_{8-4}$	max.	21 V
Common mode voltage	$V_i$	-6 to +1.5 V	
Differential mode voltage	$V_{2-3}$	max.	$\pm 5$ V
<u>Output current (peak value)</u>	$I_{OM}$	max.	50 mA
<u>Power dissipation up to <math>T_{amb} = 70^\circ\text{C}</math></u>	$P_{tot}$	max.	300 mW

Temperatures

Operating ambient temperature	$T_{amb}$	0 to +70 $^\circ\text{C}$
Storage temperature	$T_{stg}$	-65 to +150 $^\circ\text{C}$

**CIRCUIT DIAGRAM**



1. Ground
2. Inverting input
3. Non-inverting input
4. Negative supply
5. Lead frequency compensation
6. Lag frequency compensation
7. Output
8. Positive supply

**CHARACTERISTICS** at  $V_P = 12$  V;  $-V_N = 6$  V;  $T_{amb} = 25$  °C

<u>Voltage gain</u> ; $R_L \geq 100$ k $\Omega$ ; $V_O = \pm 5$ V	$G_V$	2000 to 6000 typ. 3400
<u>Input offset voltage</u> ; $R_S \leq 2$ k $\Omega$	$V_{iO}$	typ. 1.5 mV < 5 mV
<u>Input bias current</u>	$I_i$	typ. 2.5 $\mu$ A < 7.5 $\mu$ A
<u>Input offset current</u>	$I_{iO}$	typ. 0.5 $\mu$ A < 2 $\mu$ A
<u>Common mode rejection ratio</u> at $f \leq 1$ kHz; $R_S \leq 2$ k $\Omega$	CMRR	> 70 dB typ. 92 dB
<u>Input voltage range</u>	$V_i$	-4 to +0.5 V
<u>Supply current</u> at $V_O = 0$	$I_{tot}$	typ. 5 mA < 6.7 mA
<u>Differential input resistance</u>	$R_i$	> 10 k $\Omega$ typ. 32 k $\Omega$
<u>Output resistance</u>	$R_O$	typ. 200 $\Omega$ < 600 $\Omega$
<u>Power dissipation</u> at $V_O = 0$	$P_{tot}$	typ. 90 mW < 120 mW

**CHARACTERISTICS** at  $V_P = 12$  V;  $-V_N = 6$  V;  $T_{amb} = 0$  to +70 °C unless otherwise specified

<u>Voltage gain</u> ; $R_L \geq 100$ k $\Omega$ ; $V_O = \pm 5$ V	$G_V$	1500 to 7000
<u>Input offset voltage</u> ; $R_S \leq 2$ k $\Omega$	$V_{iO}$	< 6.5 mV
<u>Average input offset voltage drift</u> ; $R_S = 50$ $\Omega$	$\frac{\Delta V_{iO}}{\Delta T}$	typ. 5 $\mu$ V/°C < 20 $\mu$ V/°C
<u>Input bias current</u> at $T_{amb} = 0$ °C	$I_i$	typ. 4 $\mu$ A < 12 $\mu$ A
<u>Input offset current</u>	$I_{iO}$	< 2.5 $\mu$ A
<u>Average input offset current drift</u> at $T_{amb} = 0$ to +25 °C	$\frac{\Delta I_{iO}}{\Delta T}$	typ. 6 nA/°C < 20 nA/°C
$T_{amb} = +25$ to +70 °C	$\frac{\Delta I_{iO}}{\Delta T}$	typ. 4 nA/°C < 10 nA/°C
<u>Common mode rejection ratio</u> at $f \leq 1$ kHz; $R_S \leq 2$ k $\Omega$	CMRR	> 65 dB typ. 86 dB

## CHARACTERISTICS (continued)

Supply voltage rejection ratio

$$V_8 = +12 \text{ to } +6 \text{ V}; V_4 = -6 \text{ to } -3 \text{ V}; R_S \leq 2 \text{ k}\Omega$$

SVRR	typ.	90 $\mu\text{V/V}$
	<	300 $\mu\text{V/V}$

Peak output voltage swing at  $R_L \geq 100 \text{ k}\Omega$

$$R_L \geq 10 \text{ k}\Omega$$

$V_{OM}$	>	$\pm 5 \text{ V}$
	typ.	$\pm 5.3 \text{ V}$
$V_{OM}$	>	$\pm 3.5 \text{ V}$
	typ.	$\pm 4 \text{ V}$

Supply current at  $V_o = 0$

$I_{tot}$	typ.	5 mA
	<	7 mA

Power dissipation at  $V_o = 0$

$P_{tot}$	typ.	90 mW
	<	125 mW